ABSTRACT OF THE DISCLOSURE

Please replace the Abstract of the Disclosure with the following paragraph:

The present invention aims to provide a solid-state imaging apparatus that realizes less leakage current, high image quality and low noise during the driving operation, and manufacturing method for the same. A MOS type imaging apparatus 1 includes an imaging region 10 and a driving region 20 both formed on a p-type silicon substrate (hereinafter called an "Si substrate") 31. The imaging region 10 includes six pixels 11 to 16 disposed in a shape of a matrix having 2 rows and 3 columns. The driving region 20 includes a timing generation circuit 21, a vertical shift register 22, a horizontal shift register 23, a pixel selection circuit 24, and so on. All transistors included in the pixels 11 to 16 in the imaging region and the circuits 21 to 24 in the driving circuit region 20 are of n-channel MOS type.